

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	9	shih.inv. and wong-cheng	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L2	12	ting.inv. and wenchi	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L3	3	lee.inv. and tzyh-cheang	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	L4	476	capacitor with ((top upper) adj electrode) and ono and ((bottom lower) adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	L5	132	4 and ((silicon adj dioxide) or (aluminum adj oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	L6	24	(wide adj1 band adj1 gap) with ((titanium adj oxide) or (silicon adj oxide) or (aluminum adj oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	BRS	L7	1135	ono with ((titanium adj oxide) or (silicon adj oxide) or (aluminum adj oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS	L8	190	4 and 7	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
9	BRS	L9	0	6 and 8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB